L Number	Hits		DB	Time stamp
12	0	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2004/09/10 09:10
		and (((oxide adj nitride adj silicon) or	US-PGPUB;	
		("ONS")) with ((oxide adj nitride adj	EPO; JPO;	
		oxide) or ("ONO")))	DERWENT;	
16	36	257/\$.ccls. and ((oxide adj nitride adj	IBM_TDB USPAT;	2004/09/10 09:10
10	36	silicon) or ("ONS")) and ((oxide adj	US-PGPUB;	2004/09/10 09:10
		nitride adj oxide) or ("ONO"))	EPO; JPO;	
	' 		DERWENT;	
	^l		IBM_TDB	
17	182		USPAT;	2004/09/10 09:10
į l	' 	silicon) or ("ONS")) and ((oxide adj	US-PGPUB;	
	^l	nitride adj oxide) or ("ONO"))	EPO; JPO;	
	' 		DERWENT; IBM TDB	
18	20	 semiconductor and (((oxide adj nitride adj	USPAT;	2004/09/10 09:10
-		silicon) or ("ONS")) with ((oxide adj	US-PGPUB;	2301,03,10 03.10
	'	nitride adj oxide) or ("ONO")))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
19	22		USPAT;	2004/09/10 09:10
		silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")))	US-PGPUB; EPO; JPO;	
		INTERPORT OF CONOTH	DERWENT;	
			IBM TDB	
10	1	,,,,,,,	USPAT;	2004/09/10 09:10
		and (((oxide adj nitride adj silicon) or	US-PGPUB;	
		("ONS")) same ((oxide adj nitride adj	EPO; JPO;	
		oxide) or ("ONO")))	DERWENT;	
11	4	438/255,258,201,261,257,756,757,724.ccls.	<pre>IBM_TDB USPAT;</pre>	2004/09/10 09:11
	4	and ((oxide adj nitride adj silicon) or	US-PGPUB;	2004/09/10 09:11
		("ONS")) and ((oxide adj nitride adj	EPO; JPO;	
		oxide) or ("ONO"))	DERWENT;	
			IBM_TDB	
13	9	, , (, ,	USPAT;	2004/09/10 09:13
	}	silicon) or ("ONS")) with ((oxide adj	US-PGPUB;	
		nitride adj oxide) or ("ONO")))	EPO; JPO; DERWENT;	
			IBM TDB	
20	О		USPAT	2004/09/10 09:13
14	10	, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/09/10 09:15
ļ		silicon) or ("ONS")) same ((oxide adj	US-PGPUB;	
		nitride adj oxide) or ("ONO")))	EPO; JPO;	
ļ	Ì	! .	DERWENT; IBM TDB	
15	32	438/\$.ccls. and ((oxide adj nitride adj	USPAT;	2004/09/10 09:16
1		silicon) or ("ONS")) and ((oxide adj	US-PGPUB;	
ļ l		nitride adj oxide) or ("ONO"))	EPO; JPO;	
			DERWENT;	
	3	(("6004847") or ("5104919")	IBM_TDB	2004/07/26 14 25
	3	(("6004847") or ("5104819") or ("6274428")).PN.	USPAT	2004/07/26 14:05
۱_	524	(438/255).CCLS.	USPAT;	2002/11/01 10:08
1			US-PGPUB;	, 5_ 10.00
1]			EPO; JPO;	
1 į			DERWENT;	
1	470	(420/250) CCI C	IBM_TDB	2002/11/01 12 12
1 =	479	(438/258).CCLS.	USPAT;	2002/11/01 10:10
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	ļ		IBM_TDB	
-	271	(438/261).CCLS.	USPĀT;	2002/11/01 10:10
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
			TDM IND	L i

		L 4430 (05B)	T	100001000000000000000000000000000000000
-	1104	(438/257).CCLS.	USPAT;	2002/11/01 10:10
			US-PGPUB; EPO; JPO;	
1			DERWENT;	
	1		IBM TDB	
_	450	(438/756).CCLS.	USPAT;	2002/11/01 10:11
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	116	(438/757).CCLS.	USPAT;	2002/11/01 10:11
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	308	(438/724).CCLS.	USPĀT;	2002/11/01 10:11
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	3039	420/255 250 201 261 257 756 757 724 2010	IBM_TDB	2002/11/01 10.15
_	3039	438/255,258,201,261,257,756,757,724.ccls.	USPAT; US-PGPUB;	2002/11/01 10:15
			EPO; JPO;	<u> </u>
			DERWENT;	
			IBM_TDB	
-	14		USPĀT;	2004/09/10 09:06
		and (ONS or (oxide adj nitride adj	US-PGPUB;	
		silicon))	EPO; JPO;	
			DERWENT; IBM TDB	
_	1	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2002/11/01 10:18
	_	and ((ONS or (oxide adj nitride adj	US-PGPUB;	2002/11/01 10.10
		silicon)) same (ONO or (oxide adj nitride	EPO; JPO;	
		adj oxide)))	DERWENT;	
			IBM_TDB	
-	24	(ONS or (oxide adj nitride adj silicon))	USPAT;	2004/07/26 14:00
		<pre>same (ONO or (oxide adj nitride adj oxide))</pre>	US-PGPUB; EPO; JPO;	
		Oxide/)	DERWENT;	
			IBM TDB	
-	13	((ONS or (oxide adj nitride adj silicon))	USPAT;	2002/11/04 10:07
1		same (ONO or (oxide adj nitride adj	US-PGPUB;	
		oxide))) and semiconductor	EPO; JPO;	
		•	DERWENT;	
l _	8	(("6004847") or ("5104819") or ("6274428")	IBM_TDB USPAT	2003/04/07 12:58
	0	or ("6180457") or ("6429470") or	USPAI	2003/04/07 12:58
		("6318267") or ("5572050") or		
		("4775549")).PN.		
-	20		USPAT;	2003/10/01 08:00
		same (ONO or (oxide adj nitride adj	US-PGPUB;	
		<pre>oxide))) and (photoresist or mask)</pre>	EPO; JPO;	
			DERWENT;	
_	10	(((ONS or (oxide adj nitride adj silicon))	IBM_TDB USPAT;	2002/11/04 10:10
		same (ONO or (oxide adj nitride adj	US-PGPUB;	
		oxide))) and (photoresist or mask)) and	EPO; JPO;	
		semiconductor	DERWENT;	
	!	//20 /001\	IBM_TDB	
	191	(438/201).CCLS.	USPAT;	2002/11/04 11:17
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	((ONO or (oxide adj nitride adj oxide))	USPĀT; JPO	2003/04/07 12:34
		same (ONS or (oxide adj nitride adj		
		silicon)) same (photoresist or mask)) and		
_	0	(re-oxidiz\$6 or (second adj oxidiz\$6))	USPAT; JPO	2002/04/07 10 00
	١	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj	OSPAT; JPO	2003/04/07 12:38
ļ l		silicon))) and (photoresist or mask) and		
		(re-oxidiz\$6 or (second adj oxidiz\$6))		
		OCCOMA AAJ ONIALEYO//		L.

-	0	(ONO or (oxide adj nitride adj oxide)) and	USPAT; JPO	2003/04/07 12:38
		(ONS or (oxide adj nitride adj silicon))		
		and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6)) and		
		semiconductor		
_	66	1	USPAT; JPO	2003/04/07 12:38
		(ONS or (oxide adj nitride adj silicon))	0011117 010	2000,01,0, 12:00
-	80283	(ONO or (oxide adj nitride adj oxide)) or	USPAT; JPO	2003/04/07 12:38
		(ONS or (oxide adj nitride adj silicon))		
- ·	23	(ONO or (oxide adj nitride adj oxide))	USPAT; JPO	2003/04/07 12:38
		same (ONS or (oxide adj nitride adj		
	1	silicon))		
-	0	((ONO or (oxide adj nitride adj oxide))	USPAT; JPO	2003/04/07 12:39
	ľ	and (ONS or (oxide adj nitride adj		
		silicon))) and (photoresist or mask) and		
		(re-oxidiz\$6 or (second adj oxidiz\$6))		0000/04/07 40 44
1 -	0	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT; JPO	2003/04/07 12:41
		same (ONS or (oxide adj nitride adj		
İ		silicon))) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6))		
1_	11		USPAT; JPO	2003/04/07 12:40
•		same (ONS or (oxide adj nitride adj	0017117 010	2003/04/07 12.40
-		silicon))) and (photoresist or mask) and		
1		semiconductor		
-	22	((ONO or (oxide adj nitride adj oxide))	USPAT; JPO	2003/04/07 12:40
	!	and (ONS or (oxide adj nitride adj		
		silicon))) and (photoresist or mask) and		
		semiconductor		
-	36		USPAT; JPO	2003/04/07 12:40
		(ONS or (oxide adj nitride adj silicon)))		
		and (photoresist or mask) and (re-oxidiz\$6		
1		or (second adj oxidiz\$6))		0000 (01 (07 10 11
-	0	((ONO or (oxide adj nitride adj oxide))	USPAT; JPO	2003/04/07 12:41
		same (ONS or (oxide adj nitride adj		
		silicon))) and (photoresist or mask) and (second adj oxidiz\$6)		
1_	0		USPAT; JPO	2003/04/07 12:41
1	"	and (ONS or (oxide adj nitride adj	USIAI, UEU	2003/04/07 12.41
		silicon))) and (photoresist or mask) and		
		(second adj oxidiz\$6)		
-	10		USPAT	2003/04/08 09:24
	1	or ("6004847") or ("6429470") or		
		("6180457") or ("5104819") or ("5572050")		
		or ("6472259") or ("4775549")).PN.		
1-	1 1	("5650344").PN.	USPAT	2003/04/08 09:37
-	5	, , , , , , , , , , , , , , , , , , , ,	USPAT	2003/04/08 09:38
	_	or ("5049514") or ("5083172")).PN.	II C D A M	2002/04/10 12 51
_	8	(("6225162") or ("6388305") or ("6168987")	USPAT	2003/04/18 13:51
		or ("6133602") or ("5591681") or ("5436481") or ("6133093") or		
		("6096604")).PN.	4	
_	9		USPAT	2003/04/18 15:09
		or ("6133602") or ("5591681") or	551111	2000/04/10 10:03
		("5436481") or ("6133093") or ("6096604")		
	ļ	or ("5572050")).PN.		
-	1	("6004847").PN.	USPAT	2003/09/30 13:31
-	150		USPAT;	2003/09/30 13:38
		silicon) and (photoresist or resist or	US-PGPUB;	
		mask) and @ad<=20011130	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	100	1	USPAT;	2003/09/30 10:58
		silicon) and (photoresist) and	US-PGPUB;	
		@ad<=20011130	EPO; JPO;	
			DERWENT;	
_	21		<pre>IBM_TDB USPAT;</pre>	2003/00/20 11-00
_	"	438/\$.ccls. and ((oxide adj nitride adj silicon) same (photoresist)) and	US-PGPUB;	2003/09/30 11:08
		@ad<=20011130	EPO; JPO;	
			DERWENT;	
			IBM TDB	
		<u> </u>		

-	13829		USPAT;	2003/09/30 13:35
		(photoresist)) and @ad<=20011130	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
<u>-</u>	13	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/09/30 11:11
		and (ONS or (oxide adj nitride adj	US-PGPUB;	2000,00,00 21111
		silicon)) and (photoresist or resist or	EPO; JPO;	,
		mask) and @ad<=20011130	DERWENT;	
			IBM_TDB	
-	3	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/09/30 11:20
		and ((oxide adj nitride adj silicon) same	US-PGPUB;	
		(photoresist or resist or mask)) and	EPO; JPO;	
		@ad<=20011130	DERWENT;	
_	1	("4376672").PN.	IBM_TDB USPAT	2003/09/30 13:43
l _	982	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/09/30 13:45
		and ((silicon) same (photoresist)) and	US-PGPUB;	2003,03,30 13:33
		@ad<=20011130	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	265	438/\$.ccls. and (ONS or (oxide adj nitride	USPAT;	2003/10/01 07:57
		adj silicon)) and (photoresist or resist	US-PGPUB;	
		or mask) and @ad<=20011130	EPO; JPO;	
			DERWENT;	
_	10826	nguyen.inv.	IBM_TDB USPAT;	2003/09/30 13:38
	10020	mgaron. inv.	US-PGPUB;	2003/03/30 13:38
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	51	nguyen.inv. and (bich-yen)	USPĀT;	2003/09/30 13:38
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
l _	51	(nguyen.inv. and (bich-yen)) and motorola	IBM_TDB USPAT;	2003/09/30 13:38
	31	(inguyen: inv. and (bich-yen)) and motoroia	US-PGPUB;	2003/09/30 13:36
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2		USPAT	2003/09/30 13:49
-	9	(("4376672") or ("5665620") or ("6472259")	USPAT	2003/09/30 14:02
		or ("5104819") or ("6180457") or		
		("6168987") or ("5591681") or ("6096604") or ("5358892")).PN.		
-	1	("20020117736").PN.	US-PGPUB	2003/09/30 14:07
-	18265	438/\$.ccls. and (ONS or (oxide same	USPAT;	2003/03/30 14:07
		nitride same silicon)) and (photoresist or	US-PGPUB;	
		resist or mask) and @ad<=20011130	EPO; JPO;	
			DERWENT;	
		420 /055 050 001 051 055 555 555	IBM_TDB	
-	2092	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/10/01 07:59
		and (ONS or (oxide same nitride same silicon))	US-PGPUB;	
1		SIIICOH <i> </i>	EPO; JPO; DERWENT;	
}			IBM TDB	
-	2090	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/10/01 07:59
		and (oxide same nitride same silicon)	US-PGPUB;	
		·	EPO; JPO;	
l			DERWENT;	
		420 /055 050 004 065 055 556	IBM_TDB	
-	585	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/10/01 08:01
		and ((oxide same nitride same silicon)	US-PGPUB;	
		same photoresist)	EPO; JPO;	
			DERWENT; IBM TDB	
_	537	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/10/01 08:09
	""	and ((oxide same nitride same silicon)	US-PGPUB;	2000,10,01 00.09
		same photoresist) and @ad<=20011130	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	500	1 420 (055 050 001 051 053 756 757 704)		T 0 0 0 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0
_	537		USPAT;	2003/10/01 08:25
		and ((ONS or (oxide same nitride same	US-PGPUB;	
		silicon)) same photoresist) and	EPO; JPO;	
		@ad<=20011130	DERWENT;	
	<u> </u>		IBM_TDB	
-	0	100,200,200,202,201,100,100,101,121100101	USPAT;	2003/10/01 14:26
		same (high adj voltage adj oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	11	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/10/01 14:27
		and (high adj voltage adj oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	11	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2003/10/01 14:27
		and (high adj voltage adj oxide) and	US-PGPUB;	
		@ad<=20011120	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	36	(("ONS") or (oxide adj nitride adj	USPAT;	2004/07/26 14:01
		silicon)) same (("ONO") or (oxide adj	US-PGPUB;	2001,01,20 11101
		nitride adj oxide)) and @ad<=20011120	EPO; JPO;	1
		linetiae aaj oniae,, ana caak zooiiizo	DERWENT;	
			IBM TDB	
	19	((oxide adj nitride adj silicon) or	USPAT;	2004/07/26 14:03
	1	("ONS")) with ((oxide adj nitride adj	US-PGPUB;	2004/07/20 14:03
		oxide) or ("ONO")) and @ad<=20011120	EPO; JPO;	
		Oxide/ Of (ONO) / and Gad(-20011120	DERWENT;	
			IBM TDB	
_	36	((oxide adj nitride adj silicon) or	USPAT;	2004/07/27 07:07
-] 30	("ONS")) same ((oxide adj nitride adj	US-PGPUB:	2004/07/27 07:07
		oxide) or ("ONO")) and @ad<=20011120	EPO; JPO;	
		ONIGE, OF (ONO)) and Gad<=20011120		
			DERWENT;	
_	0	20020061658.URPN.	IBM_TDB USPAT	2004/07/27 07:02
_	1689	((oxide adj nitride adj silicon) or		
-	1089		USPAT;	2004/07/27 07:09
	•	("ONS")) and ((oxide adj nitride adj	US-PGPUB;	
ļ		oxide) or ("ONO")) and @ad<=20011120	EPO; JPO;	
			DERWENT;	
	1.50		IBM_TDB	0004/07/07 05 15
-	159	((oxide adj nitride adj silicon) or	USPAT;	2004/07/27 07:10
		("ONS")) and ((oxide adj nitride adj	US-PGPUB;	
		oxide) or ("ONO")) and @ad<=20011120 and	EPO; JPO;	
		semiconductor	DERWENT;	
L			IBM_TDB	